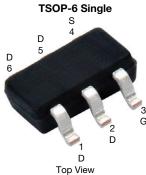
## SQ3495EV

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# Automotive P-Channel 30 V (D-S) 175 °C MOSFET

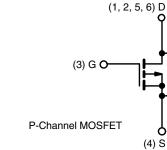


#### FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 %  $R_q$  and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



COMPLIANT HALOGEN



Marking	Code:	9F

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	-30			
$R_{DS(on)}(\Omega)$ at $V_{GS}$ = -4.5 V	0.021			
$R_{DS(on)}(\Omega)$ at $V_{GS}$ = -2.5 V	0.033			
I <sub>D</sub> (A)	-8			
Configuration	Single			
Package	TSOP-6			

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	-30	V	
Gate-source voltage		V <sub>GS</sub> ± 12		V	
Continuous drain current	T <sub>C</sub> = 25 °C	I	-8		
Continuous drain current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	-7		
Continuous source current (diode conduction)		Is	-4.5	А	
Pulsed drain current		I <sub>DM</sub>	-32		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-19.5		
Single pulse avalanche Energy		E <sub>AS</sub>	19	mJ	
	T <sub>C</sub> = 25 °C	D-	5	W	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 125 °C	PD	1.6	vv	
Operating junction and storage temperature rang	e	T <sub>J</sub> , T <sub>sta</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount <sup>b</sup>	R <sub>thJA</sub>	110	°C/W	
Junction-to-foot (drain)		R <sub>thJF</sub>	30	0/W	

#### Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$ 

b. When mounted on 1" square PCB (FR4 material)

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<b>SPECIFICATIONS</b> ( $T_C = 25 \ ^{\circ}C$	1				1			
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> =	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA		-	-	v	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-0.6	-1	-1.4	v	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, $V_{GS} = \pm 12 V$	-	-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = -30 V	-	-	-1		
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS}$ = -30 V, $T_{J}$ = 125 °C	-	-	-50	μA	
		$V_{GS} = 0 V$	$V_{DS}$ = -30 V, $T_{J}$ = 175 °C	-	-	-150		
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	V <sub>DS</sub> = -5 V	-10	-	-	Α	
Drain-source on-state resistance <sup>a</sup>		$V_{GS}$ = -4.5 V	I <sub>D</sub> = -5 A	-	0.017	0.021		
	P	$V_{GS}$ = -4.5 V	I <sub>D</sub> = -5 A, T <sub>J</sub> = 125 °C	-	-	0.030	Ω	
	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -5 A, T <sub>J</sub> = 175 °C	-	-	0.034	52	
		V <sub>GS</sub> = -2.5 V	I <sub>D</sub> = -4 A	-	0.027	0.034		
Forward transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -5 A		-	24	-	S	
Dynamic <sup>b</sup>	•	•						
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = -20 V, f = 1 MHz	-	3032	3950	pF	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	220	285		
Reverse transfer capacitance	C <sub>rss</sub>			-	217	285		
Total gate charge <sup>c</sup>	Qg			-	29	41		
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = -4.5 V	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -7.9 A	-	5.7	-	nC	
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	8.4	-	1	
Gate resistance	Rg		f = 1 MHz	2.2	5.6	9	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	20	28		
Rise time <sup>c</sup>	t <sub>r</sub>	$\begin{array}{l} V_{\text{DD}}=\text{-15 V, }R_{\text{L}}=1.9 \ \Omega\\ I_{\text{D}}\cong\text{-7.9 A, }V_{\text{GEN}}=\text{-4.5 V, }R_{\text{g}}=1 \ \Omega \end{array}$		-	51	72	1	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	71	100	ns	
Fall time <sup>c</sup>	t <sub>f</sub>			-	68	96	1	
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>	•			•			
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	-32	Α	
Forward voltage	V <sub>SD</sub>	$I_{\rm F} = -5$ A, $V_{\rm GS} = 0$ V		-	-0.8	-1.2	V	

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$ 

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

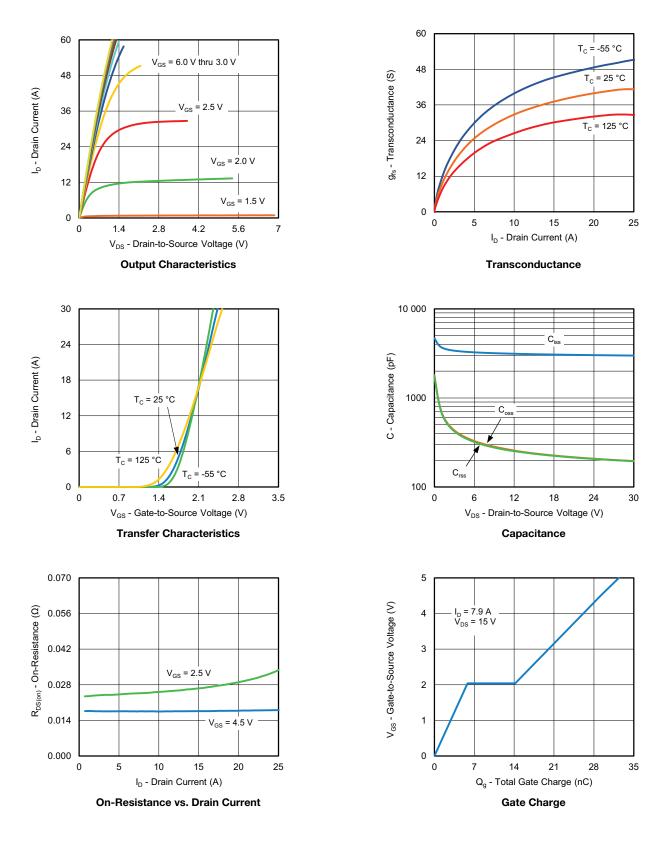
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



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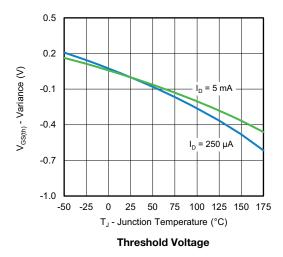
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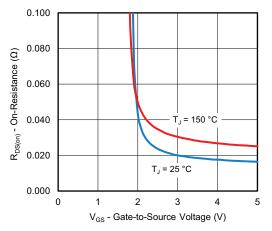


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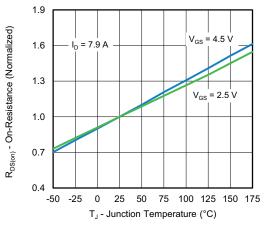
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### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)





**On-Resistance vs. Gate-to-Source Voltage** 



**On-Resistance vs. Junction Temperature** 

Note

a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

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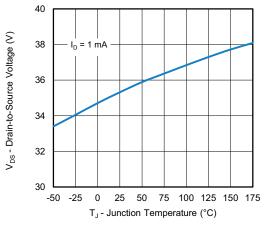
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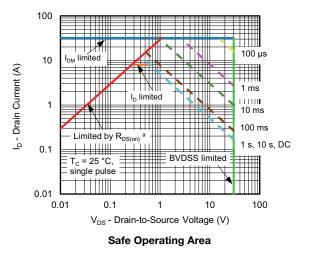
10 I<sub>s</sub> - Source Current (A) T<sub>J</sub> = 150 °C 1 T\_ = 25 °C 0.1 0.01 0 0.3 1.2 1.5 0.6 0.9 V<sub>SD</sub> - Source-to-Drain Voltage (V)

100

Source Drain Diode Forward Voltage



Drain Source Breakdown vs. Junction Temperature

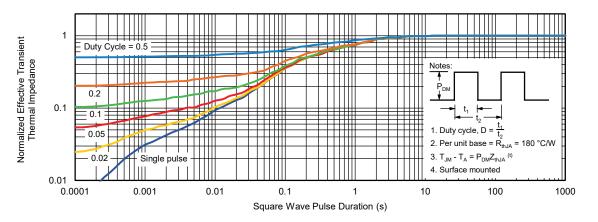




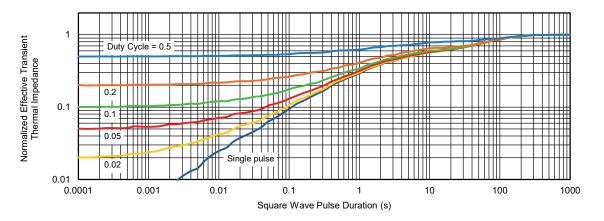
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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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Package Information

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TSOP: 5/6-LEAD JEDEC Part Number: MO-193C









6-LEAD TSOP



	MILLIMETERS			INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
<b>A</b> <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004	
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
Е	2.70	2.85	2.98	0.106	0.112	0.117	
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067	
е		0.95 BSC		0.0374 BSC			
<b>e</b> <sub>1</sub>	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	-	0.020	
L <sub>1</sub>		0.60 Ref			0.024 Ref		
L <sub>2</sub>		0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
$\theta_1$	7° Nom			7° Nom			
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

# **Application Note 826**

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**RECOMMENDED MINIMUM PADS FOR TSOP-6** 



Recommended Minimum Pads Dimensions in Inches/(mm)

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